NSN 5961-00-689-1989

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View Online at https://aerobasegroup.com/nsn/5961-00-689-1989 **Inclosure Material:** Metal **Overall Length:** 1.308 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 repetitive peak reverse voltage and 200.0 repetitive peak off-state voltage and 10.0 peak gate voltage **Current Rating Per Characteristic:** 4.70 amperes forward current, total rms megahertz **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 81349-mil-prf-19500/168 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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Mil-std (military Standard):

Mil-prf-19500 spec.